Ordering number:926C

PNP/NPN Epitaxial Planar Silicon Darlington Tranasistors

2SB882/2SD1192

Driver Applications

Applications

· Motor drivers, printer hammer drivers, relay drivers, voltage regulator control.

Features

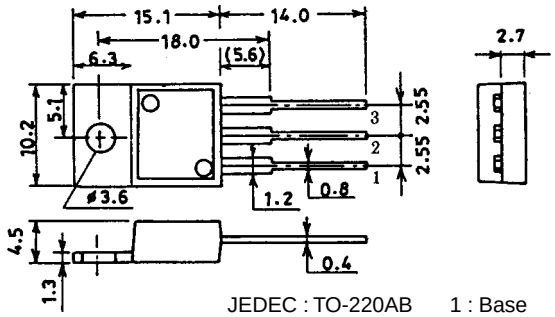
· High DC current gain.
· High current capacity and wide ASO.
· Low saturation voltage.

Package Dimensions

unit:mm

2010C

[2SB882/2SD1192]



JEDEC : TO-220AB
EIAJ : SC-46

1 : Base
2 : Collector
3 : Emitter

( ) : 2SB882

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(–)70	V
Collector-to-Emitter Voltage	V_{CEO}		(–)60	V
Emitter-to-Base Voltage	V_{EBO}		(–)6	V
Collector Current	I_C		(–)10	A
Collector Current (Pulse)	I_{CP}		(–)15	A
Collector Dissipation	P_C		1.75	W
		Tc=25˚C	40	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

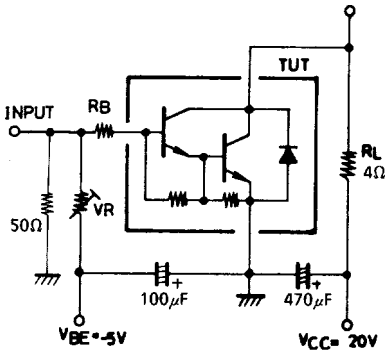
Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(–)40V, I_E=0			(–)0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(–)5V, I_C=0			(–)3.0	mA
DC Current Gain	h_{FE}	V_{CE}=(–)2V, I_C=(–)5A	2000	5000		
Gain-Bandwidth Product	f_T	V_{CE}=(–)5V, I_C=(–)5A		20		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=(–)5A, I_B=(–)10mA		0.9	(–)1.5	V
				(–)1.0		V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=(–)5A, I_B=(–)10mA			(–)2.0	V

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

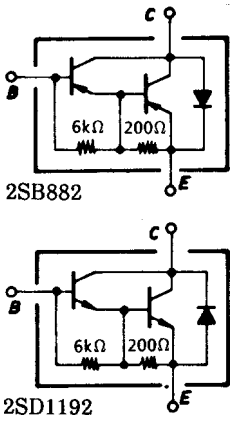
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(–)5mA, I_E=0	(–)70			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(–)50mA, R_{BE}=∞	(–)60			V
Turn-ON Time	t_{on}	See specified Test Circuit		(0.5)		μs
				0.6		μs
Storage Time	t_{stg}	See specified Test Circuit		(1.5)		μs
				3.0		μs
Fall Time	t_f	See specified Test Circuit		(1.7)		μs
				1.8		μs

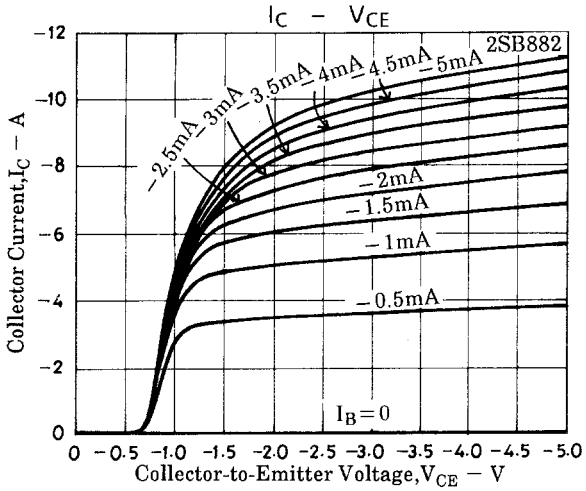
Switching Time Test Circuit

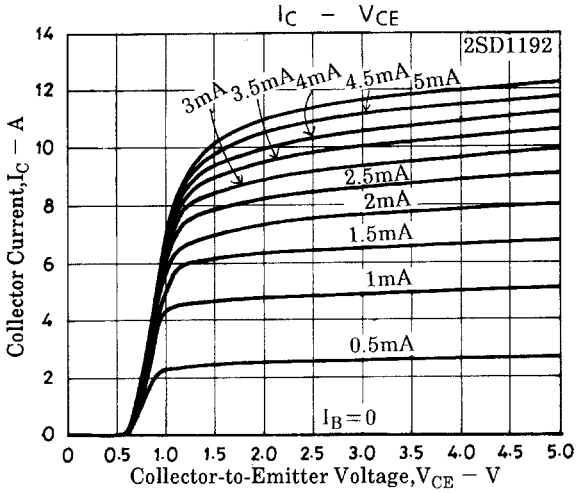


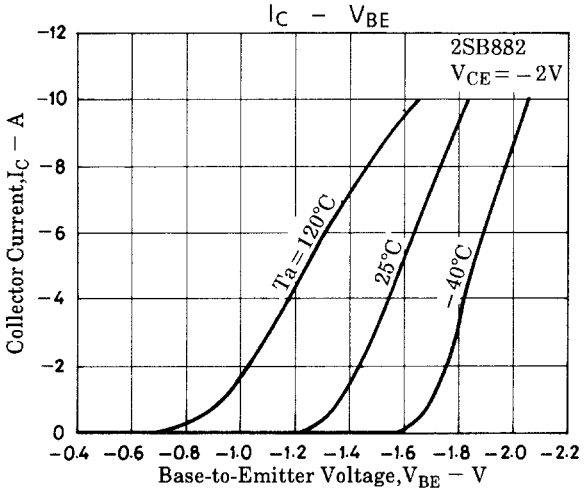
(For PNP, the polarity is reversed.)
PW=50μs, Duty Cycle≦1%
$500I_B1 = -500I_B2 = I_C = 5A$

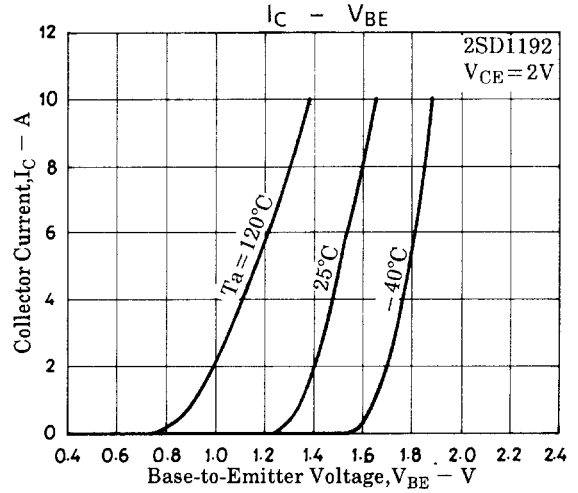
Electrical Connection

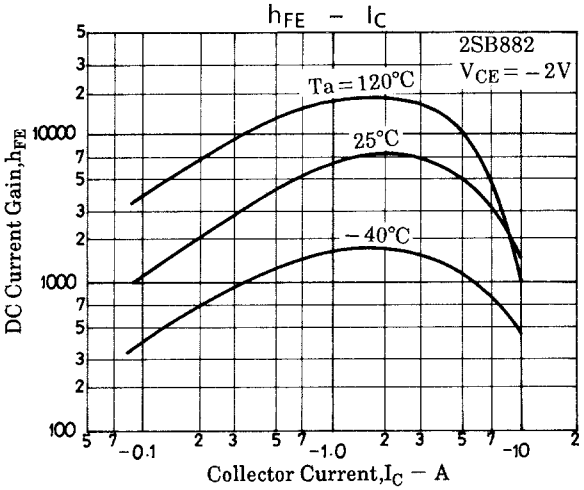


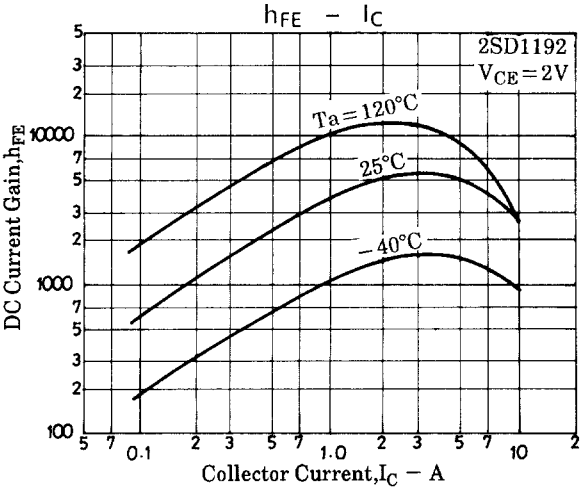


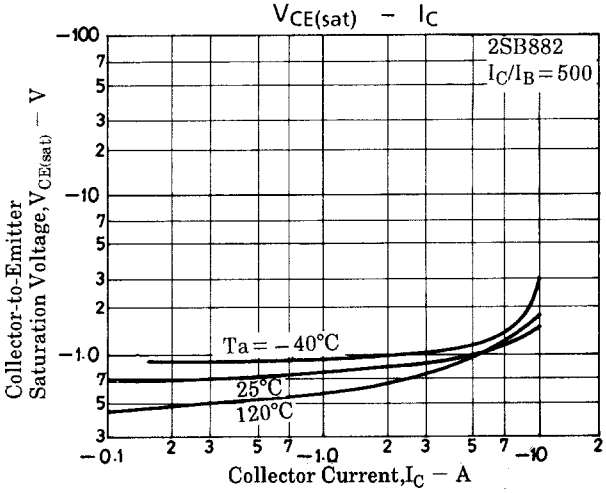


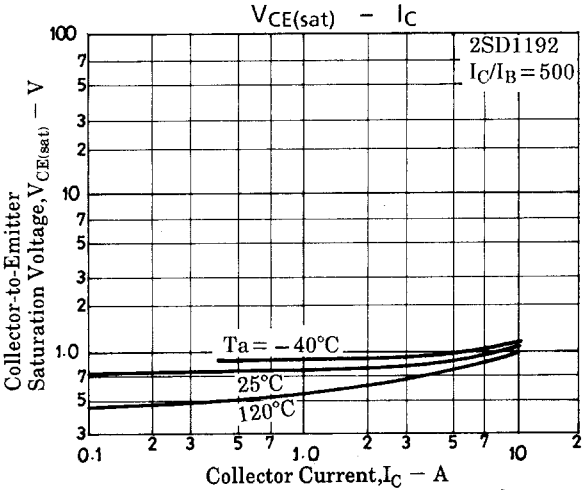


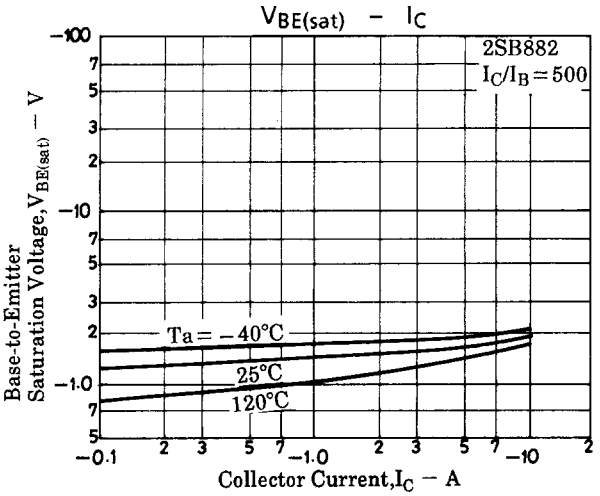


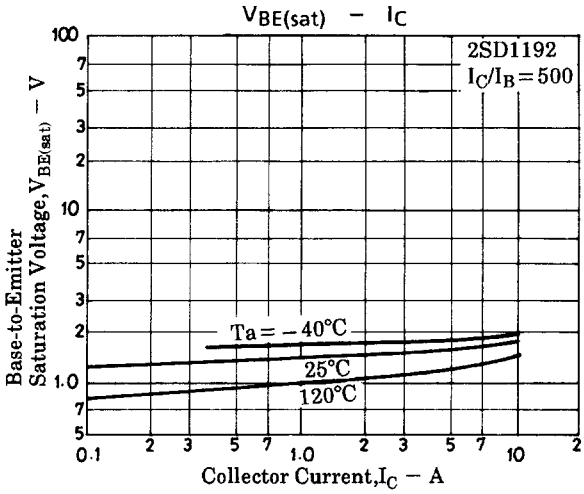

hFE – IC
2SB882
VCE = –2V
Ta = 120°C
25°C
–40°C
DC Current Gain, hFE
Collector Current, IC – A

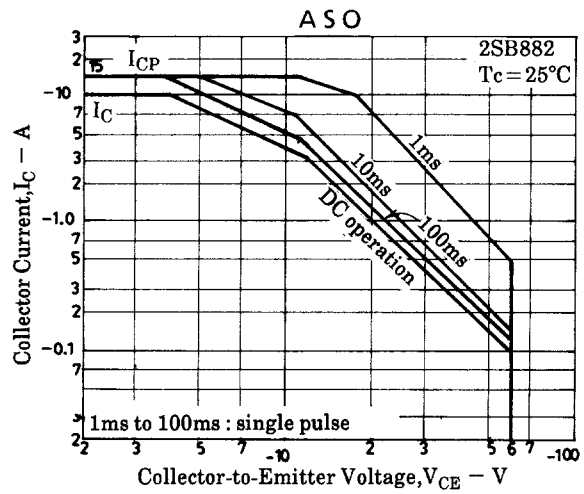

hFE – IC
2SD1192
VCE = 2V
Ta = 120°C
25°C
–40°C
DC Current Gain, hFE
Collector Current, IC – A

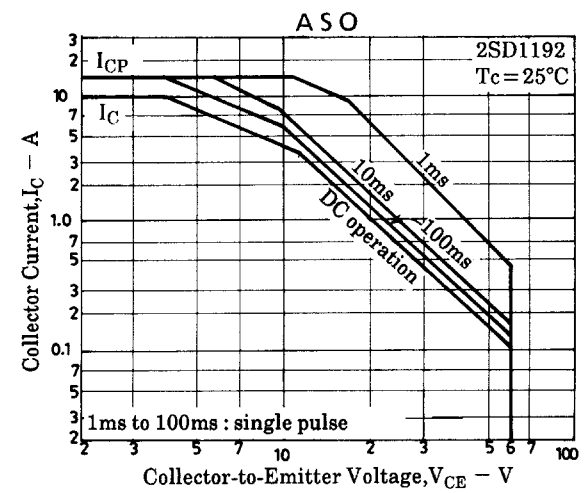

VCE(sat) – IC
2SB882
IC/IB = 500
Ta = –40°C
25°C
120°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A


VCE(sat) – IC
2SD1192
IC/IB = 500
Ta = –40°C
25°C
120°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A


VBE(sat) – IC
2SB882
IC/IB = 500
Ta = –40°C
25°C
120°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A


VBE(sat) – IC
2SD1192
IC/IB = 500
Ta = –40°C
25°C
120°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A


ASO
2SB882
Tc = 25°C
ICP
IC
1ms
10ms
100ms
DC operation
1ms to 100ms : single pulse
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V


ASO
2SD1192
Tc = 25°C
ICP
IC
1ms
10ms
100ms
DC operation
1ms to 100ms : single pulse
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V